

NPN HIGH POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/384

Devices

2N3584

2N3585

Qualified Level

JAN
JANTX
JANTXV

MAXIMUM RATINGS

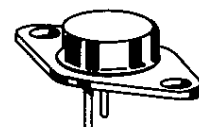
Ratings	Symbol	2N3584	2N3585	Units
Collector-Emitter Voltage	V_{CEO}	250	300	Vdc
Collector-Base Voltage	V_{CBO}	375	500	Vdc
Collector-Base Voltage	V_{CER}	300	400	Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Base Current	I_B	1.0		Adc
Collector Current	I_C	2.0		Adc
Total Power Dissipation @ $T_A = +25^{\circ}\text{C}$ (1)	P_T	2.5		W
@ $T_C = +25^{\circ}\text{C}$ (2)		35		W
Operating & Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200		$^{\circ}\text{C}$

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max.	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	5.0	$^{\circ}\text{C/W}$

1) Derate linearly @ 14.85 mW/ $^{\circ}\text{C}$ for $T_A > +25^{\circ}\text{C}$

2) Derate linearly @ 200 mW/ $^{\circ}\text{C}$ for $T_C > +25^{\circ}\text{C}$



TO-66* (TO-213AA)

*See Appendix A for
Package Outline

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = 10 \text{ mAdc}$	2N3584 2N3585	$V_{(BR)CEO}$	250 300	Vdc
Collector-Base Breakdown Voltage $I_C = 15 \text{ mAdc}$	2N3584 2N3585	$V_{(BR)CER}$	375 500	Vdc
Collector-Emitter Cutoff Current $V_{CE} = 150 \text{ Vdc}$		I_{CEO}	5.0	mAdc
Collector-Emitter Cutoff Current $V_{CE} = 300 \text{ Vdc}, V_{BE} = 1.5 \text{ Vdc}$ $V_{CE} = 400 \text{ Vdc}, V_{BE} = 1.5 \text{ Vdc}$	2N3584 2N3585	I_{CEX}	1.0 1.0	mAdc
Emitter-Base Cutoff Current $V_{EB} = 6.0 \text{ Vdc}$		I_{EBO}	0.5	mAdc

6 Lake Street, Lawrence, MA 01841

1-800-446-1158 / (978) 794-1666 / Fax: (978) 689-0803

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ELECTRICAL CHARACTERISTICS (con't)

Characteristics	Symbol	Min.	Max.	Unit
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ON CHARACTERISTICS ⁽³⁾

Forward-Current Transfer Ratio $I_C = 1.0 \text{ Adc}, V_{CE} = 10 \text{ Vdc}$ $I_C = 100 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$	h_{FE}	25 40	100	
Collector-Emitter Saturation Voltage $I_C = 1.0 \text{ Adc}, I_B = 0.125 \text{ Adc}$	$V_{CE(sat)}$		0.75	Vdc
Base-Emitter Saturation Voltage $I_C = 1.0 \text{ Adc}, I_B = 0.1 \text{ Adc}$	$V_{BE(sat)}$		1.4	Vdc

DYNAMIC CHARACTERISTICS

Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 200 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 5.0 \text{ MHz}$	$ h_{fe} $	3.0	15	
Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 1.0 \text{ Adc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz}$	h_{fe}	25	200	
Output Capacitance $V_{CB} = 10 \text{ Vdc}, I_E = 0, 100 \text{ kHz} \leq f \leq 1.0 \text{ MHz}$	C_{obo}		120	pF

SWITCHING CHARACTERISTICS

Turn-On Time $V_{CC} = 30 \text{ Vdc}; I_C = 1.0 \text{ Adc}; I_B = 100 \text{ mAdc}; R_C = 29 \Omega$	t_{on}		3.0	μs
Turn-Off Time $V_{CC} = 30 \text{ Vdc}; I_C = 1.0 \text{ Adc}; I_B = -I_B = 100 \text{ mAdc}; R_C = 29 \Omega$	t_{off}		7.0	μs

SAFE OPERATING AREA

DC Tests $T_C = +25^\circ\text{C}, 1 \text{ Cycle}, t = 1.0 \text{ s}$ Test 1 $V_{CE} = 17.5 \text{ Vdc}, I_C = 2.0 \text{ Adc}$ Test 2 $V_{CE} = 100 \text{ Vdc}, I_C = 350 \text{ mAdc}$ Test 3 $V_{CE} = 250 \text{ Vdc}, I_C = 37 \text{ mAdc}$ 2N3584 $V_{CE} = 300 \text{ Vdc}, I_C = 17 \text{ mAdc}$ 2N3585				
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(3) Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

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